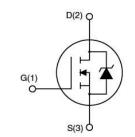


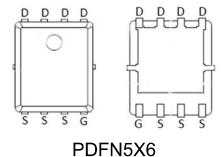
Feature

• 30V,150A

$$\begin{split} R_{DS~(ON)} &< 1.8 m~\Omega~@V_{GS} = 10V \\ R_{DS~(ON)} &< 3.2 m~\Omega~@V_{GS} = 4.5V \end{split}$$

- Advanced Trench Technology
- Lead free product is acquired
- Excellent R DS (ON) and Low Gate Charge





Application

- PWM applications
- Load Switch
- Power management

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
30H220G	AP30H220G	PDFN5X6	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (T _a =25℃)	I _D	150	Α
Continuous Drain Current (T _a =100℃)	I _D	98	А
Pulsed Drain Current (1)	I _{DM}	760	А
Single Pulsed Avalanche Energy (2)	E _{AS}	441	mJ
Power Dissipation	P _D	154	W
Thermal Resistance from Junction to Case	R _{θJC}	0.97	°C/W
Junction Temperature	TJ	150	C
Storage Temperature	T _{STG}	-55~ +150	C



MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Туре	Max	Unit	
Static Characteristics							
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30	-	-	V	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA	
Gate-body leakage current	I _{GSS}	V_{GS} = ± 20 V, V_{DS} = 0V	-	-	±100	nA	
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250μA	1	1.6	2.5	V	
Drain-source on-resistance ⁽³⁾		V _{GS} =10V, I _D =30A	-	1.4	1.8	m0	
Drain-source on-resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20A	-	2.3	3.2	mΩ	
Dynamic characteristics							
Input Capacitance	C _{iss}		-	6847	_	pF	
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V, f =1MHz	-	940	-		
Reverse Transfer Capacitance	C _{rss}	_	-	604	-		
Switching characteristics							
Turn-on delay time	t _{d(on)}	V_{DD} =15V, I_{D} =30A, R_{L} =1 Ω V_{GS} =10V, R_{G} =3 Ω	-	16	_	ns	
Turn-on rise time	t _r		-	9	-		
Turn-off delay time	$t_{d(off)}$		-	65	-		
Turn-off fall time	t _f	_	-	18	-		
Total Gate Charge	Qg	\/D0_45\/_ID_00A	-	93	-	nC	
Gate-Source Charge	Qgs	VDS=15V, ID=30A,	-	14	-		
Gate-Drain Charge	Qgd	- VGS=10V	-	21	-		
Source-Drain Diode characteristics			·				
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} =0V, I _S =30A	-	-	1.2	V	
Diode Forward current ⁽⁴⁾	Is		-	-	150	Α	

Notes:

- 1. Repetitive Rating: pulse width limited by maximum junction temperature
- 2. EAS Condition: T_J =25 $^{\circ}$ C, V_{DD} =15V, R_G =25 $^{\Omega}$,L=0.5mH, I_{AS} =42A
- 3. Pulse Test: pulse width≤300µs, duty cycle≤2%
- 4. Surface Mounted on FR4 Board,t≤10 sec



Test Circuit

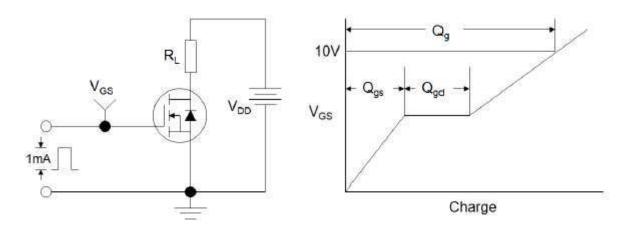


Figure1:Gate Charge Test Circuit & Waveform

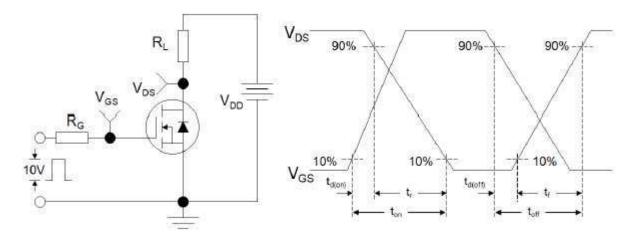


Figure 2: Resistive Switching Test Circuit & Waveforms

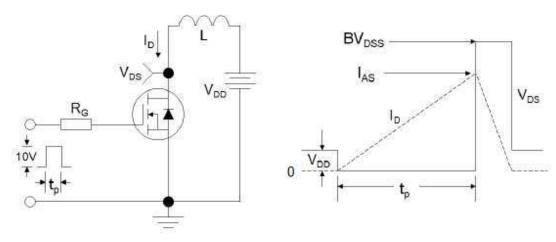


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Typical Performance Characteristics

Figure1: Output Characteristics

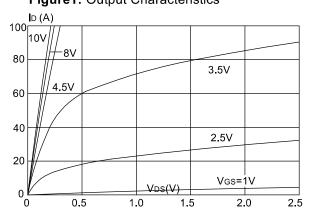


Figure 3:On-resistance vs. Drain Current

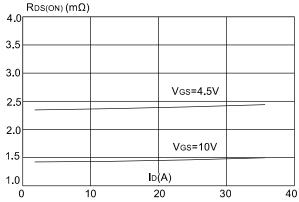


Figure 5: Gate Charge Characteristics

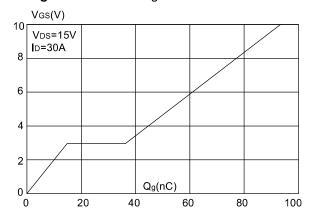


Figure 2: Typical Transfer Characteristics

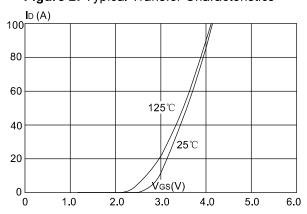


Figure 4: Body Diode Characteristics

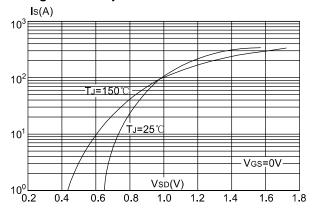
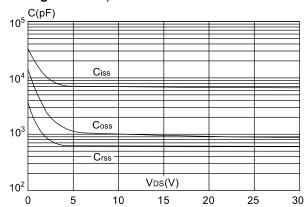


Figure 6: Capacitance Characteristics





DATA SHEET

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

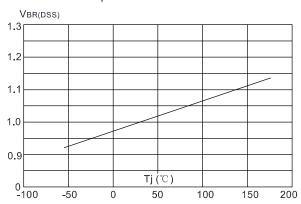


Figure 9: Maximum Safe Operating Area

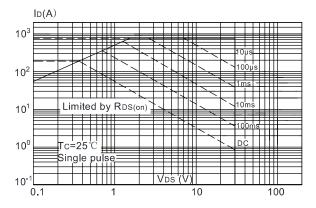


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

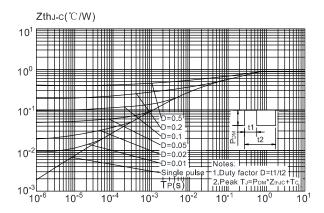


Figure 8: Normalized on Resistance vs. Junction Temperature

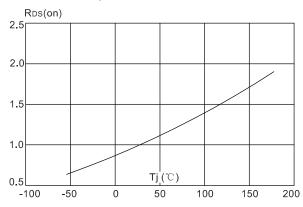
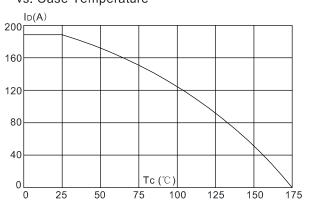
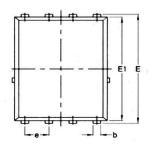


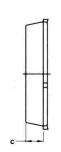
Figure 10: Maximum Continuous Drain Current vs. Case Temperature

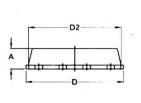


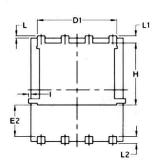


PDFN5X6 Package Information









PDFN5X6

S Y M B	COMMON						
	М	M	INCH				
O	MIN.	MAX.	MIN.	MAX.			
Α	1.03	1.17	0.0406	0.0461			
b	0.34	0.48	0.0134	0.0189			
С	0.824	0.970	0.0324	0.0382			
D	4.80	5.40	0.1890	0.2126			
D1	4.11	4.31	0.1618	0.1697			
D2	4.80	5.00	0.1890	0.1969			
E	5.95	6.15	0.2343	0.2421			
E1	5.65	5.85	0.2224	0.2303			
E2	1.60	<u>91—19</u>	0.0630	2-3			
е	1.27	BSC	0.05	BSC			
L	0.05	0.25	0.0020	0.0098			
L1	0.38	0.50	0.0150	0.0197			
L2	0.38	0.50	0.0150	0.0197			
Н	3.30	3.50	0.1299	0.1378			
1	-	0.18	<u> </u>	0.0070			